Approved for use through 07/31/2006. OMB 0651-0031 U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number Application Number 10/625,068 TRANSMITTAL Filing Date July 22, 2003 First Named Inventor **FORM** Arup Bhattacharyya Art Unit 2829 **Examiner Name** Christian D. Wilson (to be used for all correspondence after initial filing) Attorney Docket Number MI22-2362 Total Number of Pages in This Submission **ENCLOSURES** (Check all that apply) After Allowance Communication to TC Fee Transmittal Form Drawing(s) Appeal Communication to Board Licensing-related Papers Fee Attached of Appeals and Interferences Appeal Communication to TC Petition Amendment/Reply (Appeal Notice, Brief, Reply Brief) Petition to Convert to a Proprietary Information After Final Provisional Application Power of Attorney, Revocation Status Letter Affidavits/declaration(s) Change of Correspondence Address Other Enclosure(s) (please Identify Terminal Disclaimer Extension of Time Request below): Return Receipt Postcard; Check - \$100.00; Request for Refund **Express Abandonment Request** Request for Certificate of Correction; Certificate of Correction CD, Number of CD(s) Information Disclosure Statement Landscape Table on CD Certified Copy of Priority Remarks Document(s) U.S. Patent No. 6,908,798 Reply to Missing Parts/ Issued: June 21, 2005 Incomplete Application Certificate Reply to Missing Parts under 37 CFR 1.52 or 1.53 MAY 2 6 2006

	David G	. Latwesen, Ph.D.							
Date	te 5/22/06				Reg. No.	o. 38,533			
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SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

Firm Name

Signature

Printed name

Wells St. John P.S.

This collection of information is required by 37 CFR 1.5. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

or Correction

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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

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Design	200	100	100	50	130			
Plant	200	100	300	150	160			
Reissue	300	150	500	250	600			
Provisional	200	100	0	0	0			
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SUBMITTED BY								
Signature	7			Registration No.	20.522	Tele	phone (509) 624-4276	
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SUBMITTED BY				
Signature	19	 Registration No. (Attorney/Agent) 38,533	Telephon	e (509) 624-4276
Name (Print/Type)	David G. Latwesen, Ph.D.		Date	127/06

This collection of information is required by 37 CFR 1.136. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 30 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.



Patent No	6,908,798 B1
Patent Issue Date	
Application Serial No	
Filing Date	
Assignee	
Inventorship	
Attorney's Docket No	
Title: "Methods of Making Semiconductor	
Constructions"	•

REQUEST FOR CERTIFICATE OF CORRECTION OF PATENT FOR APPLICANT MISTAKES and PTO MISTAKES (37 C.F.R. §§ 1.322(a) and 1.323)

To:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

ATTN:

Decision and Certificate of Correction Branch of the Patent Issue Division

From:

David G. Latwesen, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)

Wells St. John P.S.

601 W. First Avenue, Suite 1300

Spokane, WA 99201-3828

Sir:

It is hereby requested that a Certificate of Correction be issued with respect to Patent No. 6,908,798 B1, granted June 21, 2005, in accordance with the Certificate of Correction form attached hereto in duplicate.

It is noted that errors appear in this patent of a typographical nature of character, as more fully described below. The errors occurred in good faith. Correction thereof does not involve such changes in the patent as would constitute new matter or would require re-examination.

05/25/2006 EAREGAY1 00000068 6908798

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Other errors listed on the Certificate of Correction form were apparently incurred through the fault of the PTO as will be disclosed by the records of files in the Office.

Attached hereto, in duplicate, is Form PTO-1050, with at least one copy being suitable for printing.

The exact page and line number where the errors occur in the application file are:

- Page 5, paragraph [0009], line 10 in the Specification/Col. 3, line
 22 in the issued patent;
- Page 7, paragraph [0016], line 1 in the Specification/Col. 4, line20 in the issued patent.

Enclosed is a check in the amount of \$100.00, as required by 37 CFR 1.20(a).

Respectfully submitted,

By:

David G. Latwesen, Ph.D.

Reg. No. 38,533

Page 1 of 1

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

: 6,908,798 B1

APPLICATION NO.: 10/625,068

ISSUE DATE

: June 21, 2005

INVENTOR(S)

Arup Bhattacharyya

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the References Cited:

Col. 2, line 14 -

Replace "Kim, C.H. et al., "A New High -Performance Poly3-Si TFT" With --Kim, C.H. et al, "A New High -Performance Poly-Si TFT--

In the Specification:

Col. 2, line 44 -

Replace ""High Performance Sub-100 nm Si TFT by Pattem-" With -- "High Performance Sub-100 nm Si TFT by Pattern---

Col. 2. line 54 -

Replace "islands for device channel regions. Nickelinduced-lateral" With --islands for device channel regions. Nickel-induced-lateral---

Col. 3, line 22 -

Replace "Digest, 2002, 00. 98-99; and Huang, L. J. et al.," With -- Digest, 2002, pp. 98-99; and Huang, L. J. et al., --

Col. 4, line 20 -

Replace "FIG. 2 is a view of the FIG. 1 wafer shown at a processing" With --FIG. 2 is a view of the FIG. 1 fragment shown at a processing--

Col. 10, line 66 -

Replace "similar numbering will be used as is used above In" With --similar numbering will be used as is used above in--

MAILING ADDRESS OF SENDER (Please do not use customer number below):

Wells St. John P.S. 601 W. 1st Avenue, Suite 1300 Spokane, WA 99201

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Page __1_ of __1_

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